

TN6727A



PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1A. Sourced from Process 77. See TN6726A for characteristics.

Absolute Maximum Ratings*

T_{A = 25°C} unless otherwise noted

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	1.5	Α
T _{J, Tstg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

Thermal Characteristics ____ T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN6727A	
P _D	Total Device Dissipation Derate above 25°C	1 8	W mW/°C
R _θ JC	Thermal Resistance, Junction to Case	50	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	125	°C/W

¹⁾ These ratings are based on a maximum junction temperature of 150°C.

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

PNP General Purpose Amplifier

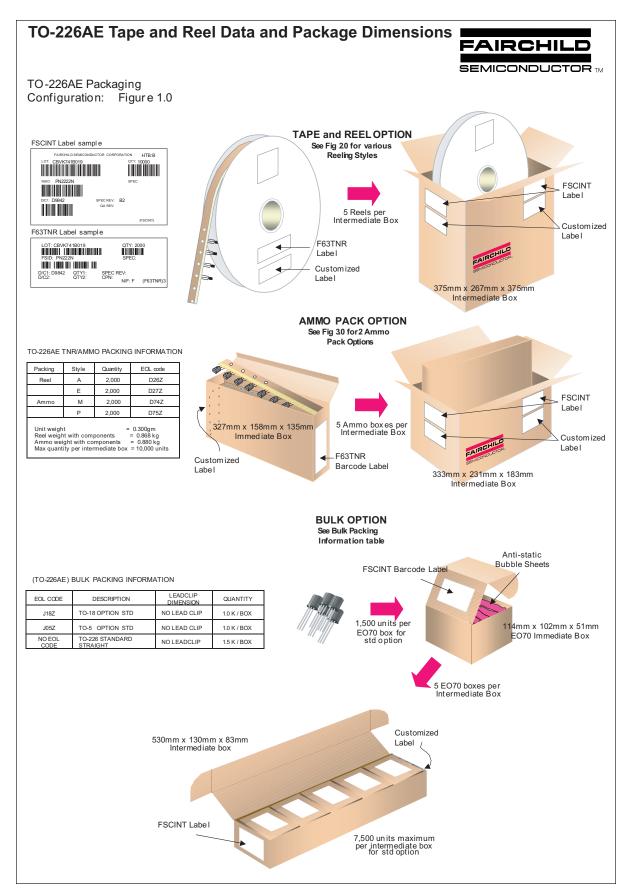
(continued)

Electrical Characteristics

 $T_{\text{A}\,=\,25^{\circ}\text{C}\,\text{unless otherwise noted}}$

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	40		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1 mA	50		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 1 mA	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 50 V		100	nA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5 V		100	nA
ON CHAI	RACTERISTICS*				
h _{FE}	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 1A, V_{CE} = 1 \text{ V}$	55 60 50	250	-
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		0.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 1 V		1.2	V
SMALL S	IGNAL CHARACTERISTICS				
C _{cb}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		30	pF
h _{fe}	Small Signal Current Gain	I _C = 50 mA,V _{CE} = 10 V, f=20MHz	2.5	25	-

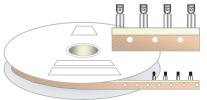
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1.0%



TO-226AE Tape and Reel Data and Package Dimensions, continued

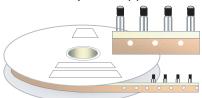
TO-226AE Reeling Style Configuration: Figure 2.0

Machine Option"A" (H)



Style "A", D26Z, D70Z (s/h)

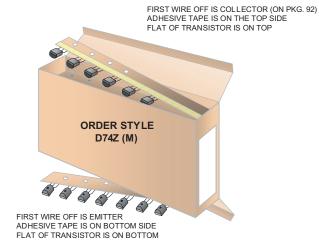
Machine Option"E" (J)



Style "E", D27Z, D71Z (s/h)

TO-226AE Radial Ammo Packaging

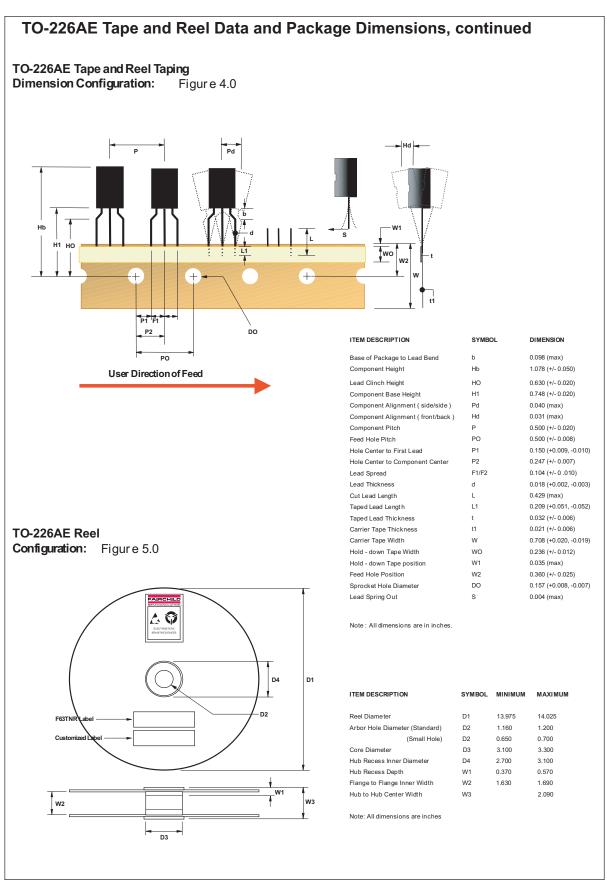
Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92)
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

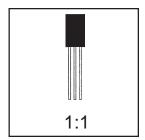
ORDER STYLE
D75Z (P)

FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP



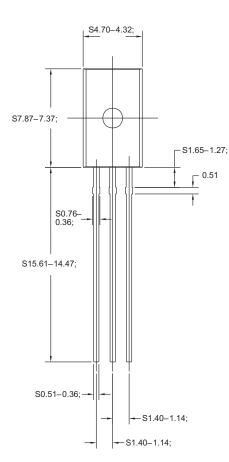
TO-226AE Tape and Reel Data and Package Dimensions, continued TO-226AE (FS PKG Code 95, 99)

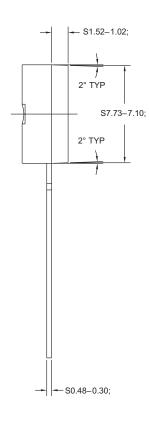




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

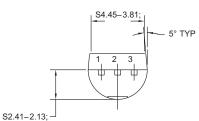
Part Weight per unit (gram): 0.300





절	99	95	
1	Е	Е	
2	В	С	
3	С	В	

For leadformed option ordering, refer to Tape & Reel data information.



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